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National Semiconductor

LF155/LF156/LF256/LF257/LF355/LF356/LF357 **JFET Input Operational Amplifiers**

General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET[™] Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Features

Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance-very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers



- Photocell amplifiers
- Sample and Hold circuits

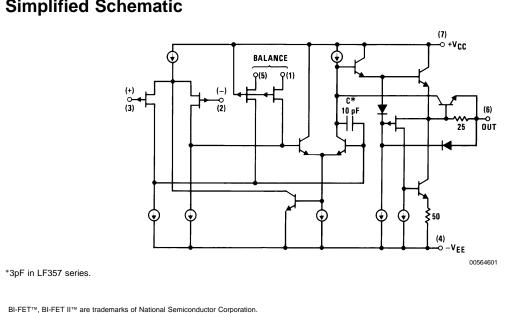
Common Features

- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High input impedance: $10^{12}\Omega$
- Low input noise current: 0.01 pA/√Hz
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

Uncommon Features

	LF155/ LF355	LF156/ LF256/ LF356	LF257/ LF357 (A _v =5)	Units
Extremely fast settling time to 0.01%	4	1.5	1.5	μs
Fast slew rate	5	12	50	V/µs
 Wide gain bandwidth 	2.5	5	20	MHz
 Low input noise voltage 	20	12	12	nV/√Hz





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December 2001

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

	LF155/6	LF256/7/LF356B	LF355/6/7	
Supply Voltage	±22V	±22V	±18V	
Differential Input Voltage	±40V	±40V	±30V	
Input Voltage Range (Note 2)	±20V	±20V	±16V	
Output Short Circuit Duration	Continuous	Continuous	Continuous	
TJMAX				
H-Package	150°C	115°C	115°C	
N-Package		100°C	100°C	
M-Package		100°C	100°C	
Power Dissipation at $T_A = 25^{\circ}C$ (Notes				
1, 8)				
H-Package (Still Air)	560 mW	400 mW	400 mW	
H-Package (400 LF/Min Air Flow)	1200 mW	1000 mW	1000 mW	
N-Package		670 mW	670 mW	
M-Package		380 mW	380 mW	
Thermal Resistance (Typical) θ_{JA}				
H-Package (Still Air)	160°C/W	160°C/W	160°C/W	
H-Package (400 LF/Min Air Flow)	65°C/W	65°C/W	65°C/W	
N-Package		130°C/W	130°C/W	
M-Package		195°C/W	195°C/W	
(Typical) θ _{JC}				
H-Package	23°C/W	23°C/W	23°C/W	
Storage Temperature Range	–65°C to +150°C	–65°C to +150°C	–65°C to +150°0	
Soldering Information (Lead Temp.)				
Metal Can Package				
Soldering (10 sec.)	300°C	300°C	300°C	
Dual-In-Line Package				
Soldering (10 sec.)	260°C	260°C	260°C	
Small Outline Package				
Vapor Phase (60 sec.)		215°C	215°C	
Infrared (15 sec.)		220°C	220°C	
See AN-450 "Surface Mounting Methods	s and Their Effect on P	roduct Reliability" for	other methods of	
soldering surface mount devices.		-		
ESD tolerance				
(100 pF discharged through 1.5k Ω)	1000V	1000V	1000V	

DC Electrical Characteristics

(Note 3)

Symbol	Parameter	Conditions	LF155/6			LF256/7 LF356B			LF355/6/7			Units
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Vos	Input Offset Voltage	R _S =50Ω, T _A =25°C		3	5		3	5		3	10	mV
		Over Temperature			7			6.5			13	mV
$\Delta V_{OS} / \Delta T$	Average TC of Input Offset Voltage	R _S =50Ω		5			5			5		µV/°C
$\Delta TC/\Delta V_{OS}$	Change in Average TC with V _{OS} Adjust	R _S =50Ω, (Note 4)		0.5			0.5			0.5		µV/°C per mV
l _{os}	Input Offset Current	T _J =25°C, (Notes 3, 5)		3	20		3	20		3	50	pА
	T _J ≤T _{HIGH}				20			1			2	nA

DC Electrical Characteristics (Continued)

Symbol	Parameter	Conditions	LF155/6			LF256/7 LF356B			LF355/6/7			Units
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
I _B	Input Bias Current	T _J =25°C, (Notes 3, 5)		30	100		30	100		30	200	pА
		T _J ≤T _{HIGH}			50			5			8	nA
R _{IN}	Input Resistance	T _J =25°C		10 ¹²			10 ¹²			10 ¹²		Ω
A _{VOL}	Large Signal Voltage $V_S = \pm 15V$, $T_A = 25^{\circ}C$ 50Gain $V_Q = \pm 10V$, $R_L = 2k$		50	200		50	200		25	200		V/mV
		Over Temperature	25			25			15			V/mV
Vo	Output Voltage Swing	V _S =±15V, R _L =10k	±12	±13		±12	±13		±12	±13		V
		$V_{S}=\pm 15V, R_{L}=2k$	±10	±12		±10	±12		±10	±12		V
V _{CM}	Input Common-Mode Voltage Range	V _S =±15V	±11	+15.1 –12		±11	±15.1 –12		+10	+15.1 –12		V V
CMRR	Common-Mode Rejection Ratio		85	100		85	100		80	100		dB
PSRR	Supply Voltage Rejection Ratio	(Note 6)	85	100		85	100		80	100		dB

DC Electrical Characteristics

 $T_A = T_J = 25^{\circ}C, V_S = \pm 15V$

Parameter	LF155		LF355		LF156/256	/257/356B	LF	356	LF	Units	
Faranieter	Тур	Max	Тур	Max	Тур	Max	Тур	Max	Тур	Max	Units
Supply Current	2	4	2	4	5	7	5	10	5	10	mA

AC Electrical Characteristics

 $T_{A} = T_{J} = 25^{\circ}C, V_{S} = \pm 15V$

Symbol	Parameter	Conditions	LF155/355	LF156/256/ 356B	LF156/256/356/ LF356B	LF257/357	Units
			Тур	Min	Тур	Тур	
SR	Slew Rate	LF155/6:	5	7.5	12		V/µs
		A _V =1,					
		LF357: A _V =5				50	V/µs
GBW	Gain Bandwidth Product		2.5		5	20	MHz
t _s	Settling Time to 0.01%	(Note 7)	4		1.5	1.5	μs
e _n	Equivalent Input Noise	R _s =100Ω					
	Voltage	f=100 Hz	25		15	15	nV/√Hz
		f=1000 Hz	20		12	12	nV/√Hz
i _n	Equivalent Input Current	f=100 Hz	0.01		0.01	0.01	pA/√Hz
	Noise	f=1000 Hz	0.01		0.01	0.01	pA/√Hz
C _{IN}	Input Capacitance		3		3	3	pF

Notes for Electrical Characteristics

Note 1: The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T_{JMAX} , θ_{JA} , and the ambient temperature, T_A . The maximum available power dissipation at any temperature is $P_D=(T_{JMAX}-T_A)/\theta_{JA}$ or the 25°C P_{dMAX} , whichever is less.

Note 2: Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

Note 3: Unless otherwise stated, these test conditions apply:

Notes for Electrical Characteristics (Continued)

	LF155/156	LF256/257	LF356B	LF355/6/7
Supply Voltage, V _S	$\pm 15V \le V_S \le \pm 20V$	$\pm 15V \le V_S \le \pm 20V$	$\pm 15V \le V_S \pm 20V$	V _S = ±15V
T _A	$-55^{\circ}C \le T_A \le +125^{\circ}C$	$-25^{\circ}C \le T_A \le +85^{\circ}C$	$0^{\circ}C \le T_A \le +70^{\circ}C$	$0^{\circ}C \le T_{A} \le +70^{\circ}C$
T _{HIGH}	+125°C	+85°C	+70°C	+70°C

and V_{OS} , I_B and I_{OS} are measured at V_{CM} = 0.

Note 4: The Temperature Coefficient of the adjusted input offset voltage changes only a small amount (0.5µV/°C typically) for each mV of adjustment from its original unadjusted value. Common-mode rejection and open loop voltage gain are also unaffected by offset adjustment.

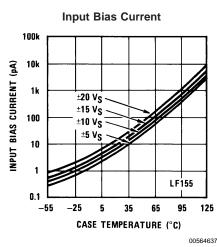
Note 5: The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T_J . Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, Pd. $T_J = T_A + \theta_{JA}$ Pd where θ_{JA} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

Note 6: Supply Voltage Rejection is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

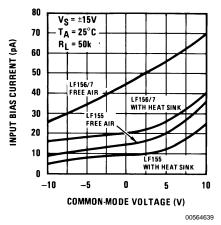
Note 7: Settling time is defined here, for a unity gain inverter connection using $2 k\Omega$ resistors for the LF155/6. It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 10V step input is applied to the inverter. For the LF357, $A_V = -5$, the feedback resistor from output to input is $2k\Omega$ and the output step is 10V (See Settling Time Test Circuit).

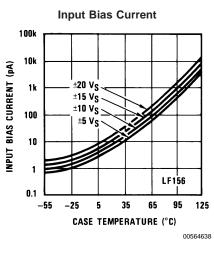
Note 8: Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the part to operate outside guaranteed limits.

Typical DC Performance Characteristics Curves are for LF155 and LF156 unless otherwise specified.

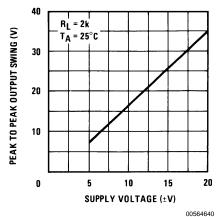




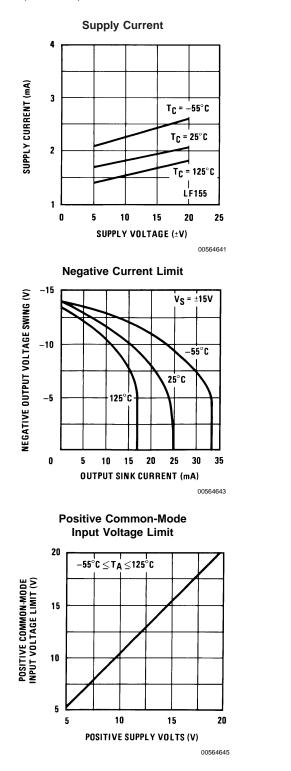


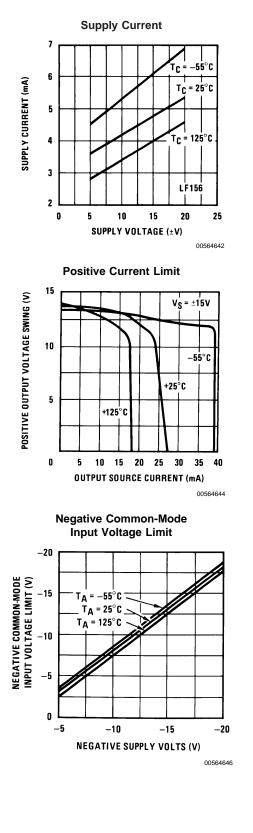


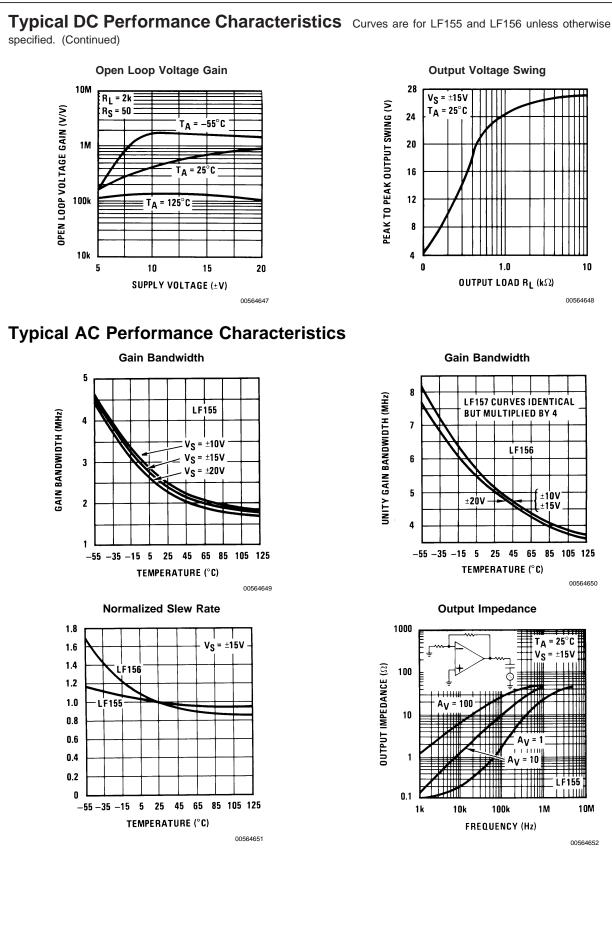


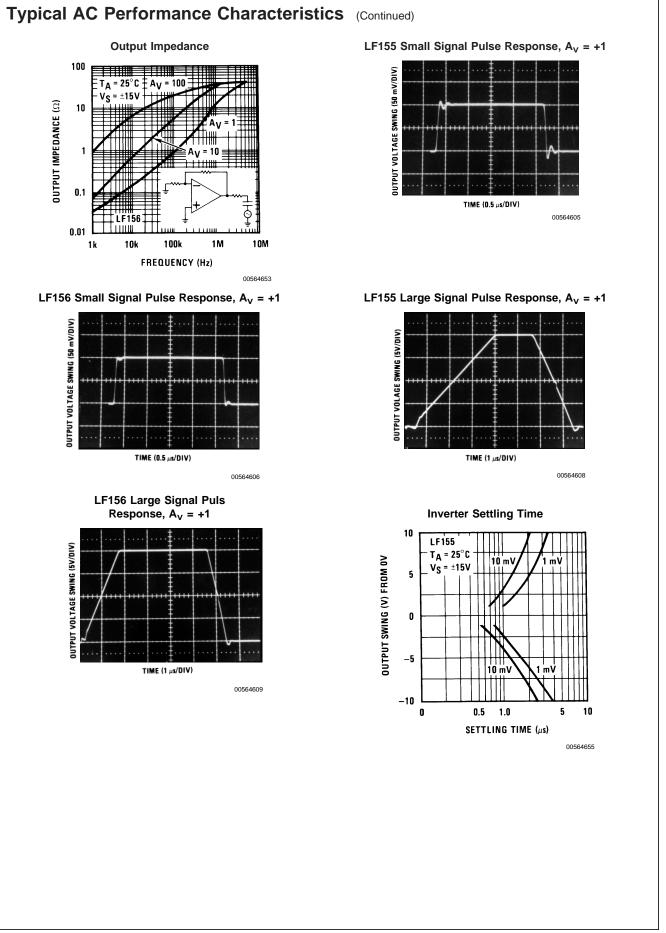


Typical DC Performance Characteristics Curves are for LF155 and LF156 unless otherwise specified. (Continued)



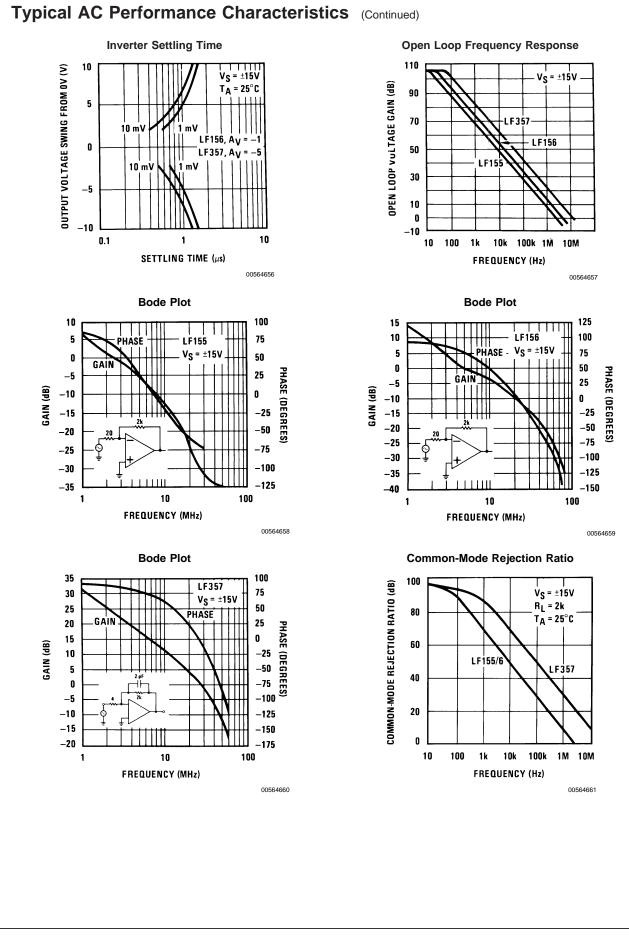


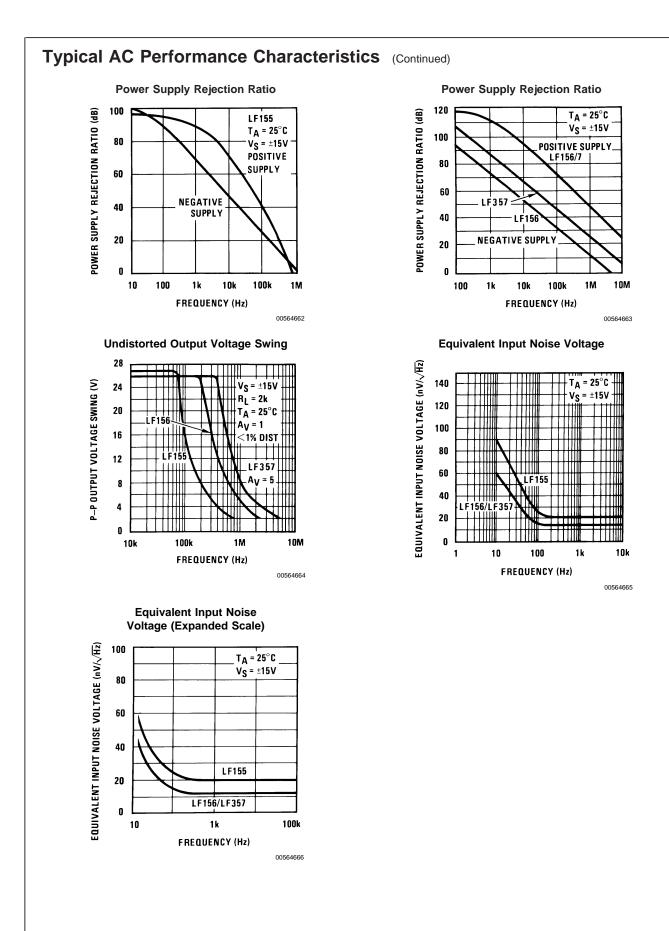




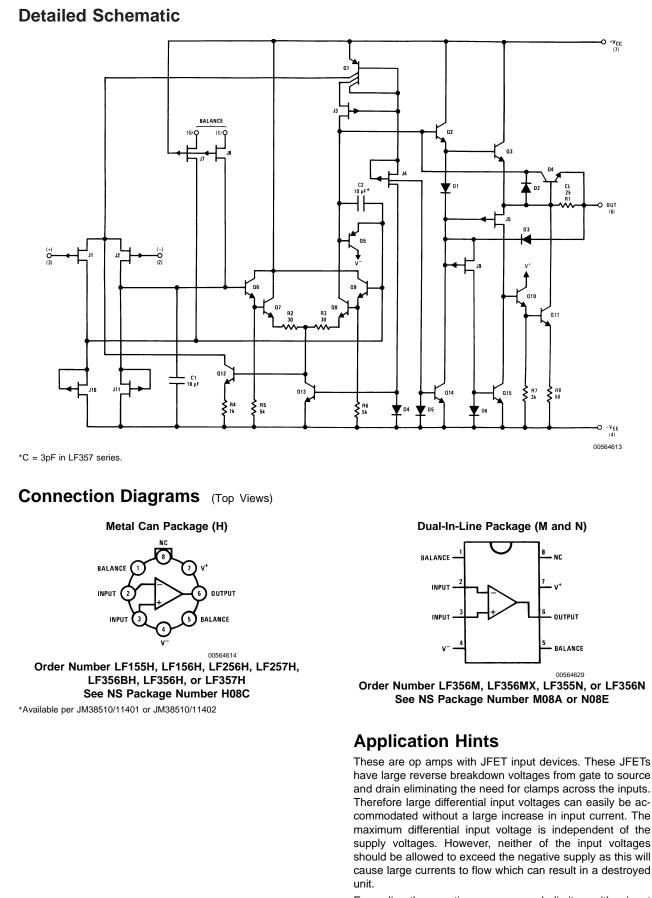
LF155/LF156/LF256/LF257/LF355/LF356/LF357







LF155/LF156/LF256/LF257/LF355/LF356/LF357



Exceeding the negative common-mode limit on either input will force the output to a high state, potentially causing a

LF155/LF156/LF256/LF257/LF355/LF356/LF357

Application Hints (Continued)

reversal of phase to the output. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

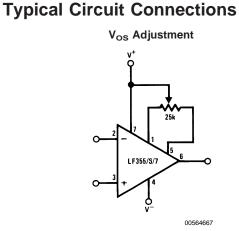
These amplifiers will operate with the common-mode input voltage equal to the positive supply. In fact, the common-mode voltage can exceed the positive supply by approximately 100 mV independent of supply voltage and over the full operating temperature range. The positive supply can therefore be used as a reference on an input as, for example, in a supply current monitor and/or limiter.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

All of the bias currents in these amplifiers are set by FET current sources. The drain currents for the amplifiers are therefore essentially independent of supply voltage.

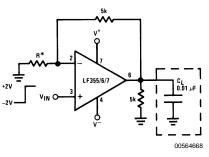
As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pickup" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.



- V_{OS} is adjusted with a 25k potentiometer
- The potentiometer wiper is connected to V⁺
- For potentiometers with temperature coefficient of 100 ppm/°C or less the additional drift with adjust is $\approx 0.5 \mu V/$ °C/mV of adjustment
- Typical overall drift: 5µV/°C ±(0.5µV/°C/mV of adj.)

Driving Capacitive Loads



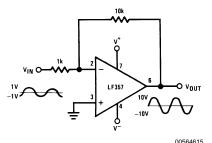
* LF155/6 R = 5k

LF357 R = 1.25k

Due to a unique output stage design, these amplifiers have the ability to drive large capacitive loads and still maintain stability. $C_{L(MAX)}\simeq 0.01 \mu F.$ Overshoot $\leq 20\%$

Settling time $(t_s) \approx 5\mu s$

LF357. A Large Power BW Amplifier



For distortion \leq 1% and a 20 Vp-p V_{OUT} swing, power bandwidth is: 500kHz.

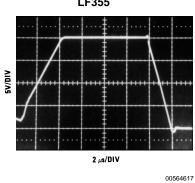
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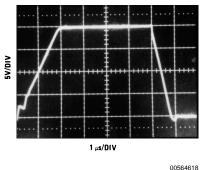
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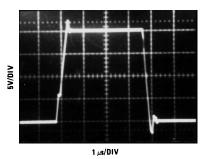
Typical Applications Settling Time Test Circuit 2k, 0.1% 15\ 2k, 0.1% 400, 0.1% 10V LF355/6/7 4416 O VOUT 5k, 0.1 1.0k, 0.1 SUMMING NODE 5k, 0.1% 2N4416 +15V OSCILLOSCOPE 00564616 Settling time is tested with the LF155/6 connected as unity gain inverter and LF357 connected for $A_V = -5$ FET used to isolate the probe capacitance Output = 10V step $A_V = -5$ for LF357 Large Signal Inverter Output, V_{OUT} (from Settling Time Circuit) LF355



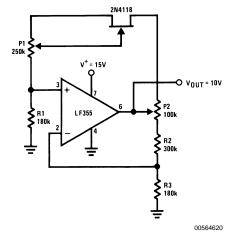






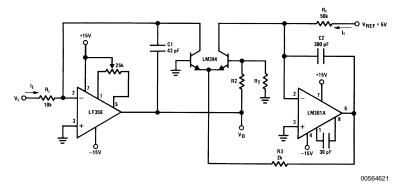


Low Drift Adjustable Voltage Reference



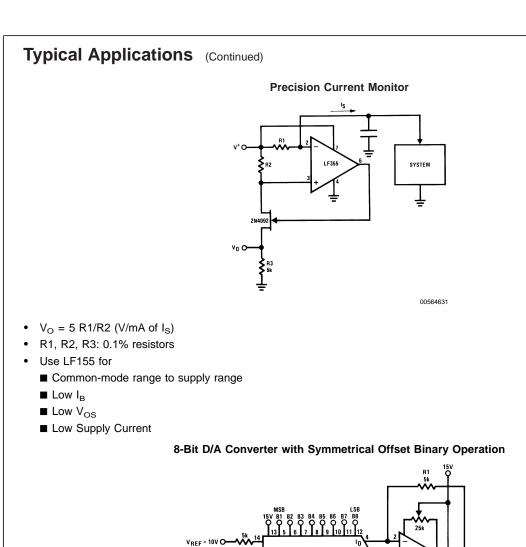
- $\Delta V_{OUT}/\Delta T = \pm 0.002\%^{\circ}C$
- All resistors and potentiometers should be wire-wound
- P1: drift adjust
- P2: V_{OUT} adjust
- Use LF155 for
 - Low I_B
 - Low drift
 - Low supply current

Fast Logarithmic Converter



- Dynamic range: $100\mu A \le I_i \le 1mA$ (5 decades), $|V_O| = 1V$ /decade
- Transient response: $3\mu s$ for $\Delta I_i = 1$ decade
- C1, C2, R2, R3: added dynamic compensation
- + V_{OS} adjust the LF156 to minimize quiescent error
- R_T: Tel Labs type Q81 + 0.3%/°C

$$V_{OUT}| = \left[1 + \frac{R2}{R_T}\right] \frac{kT}{q} \text{ in } V_i \left[\frac{R_r}{V_{REF Ri}}\right] = \log V_i \frac{1}{R_i l_r} R2 = 15.7k, R_T = 1k, 0.3\%/°C \text{ (for temperature compensation)}$$



- -15V
- R1, R2 should be matched within ±0.05%
- Full-scale response time: 3µs

Eo	B1	B2	B 3	Β4	B5	B6	B7	B 8	Comments
+9.920	1	1	1	1	1	1	1	1	Positive Full-Scale
+0.040	1	0	0	0	0	0	0	0	(+) Zero-Scale
-0.040	0	1	1	1	1	1	1	1	(-) Zero-Scale
-9.920	0	0	0	0	0	0	0	0	Negative Full-Scale

DAC08

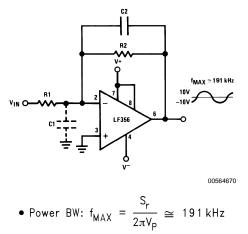
0.01 μF

LF356

-15\

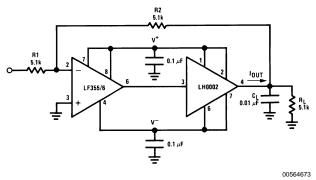
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Wide BW Low Noise, Low Drift Amplifier



• Parasitic input capacitance C1 ≃ (3pF for LF155, LF156 and LF357 plus any additional layout capacitance) interacts with feedback elements and creates undesirable high frequency pole. To compensate add C2 such that: R2 C2 ≃ R1 C1.

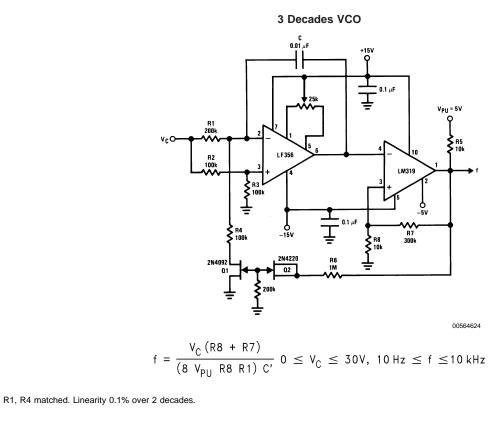




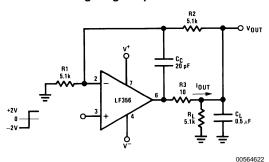
• $I_{OUT(MAX)} \approx 150 \text{mA}$ (will drive $R_L \ge 100 \Omega$)

•
$$\frac{\Delta V_{OUT}}{\Delta T} = \frac{0.15}{10^{-2}} V/\mu s$$
 (with C_L shown)

• No additional phase shift added by the current amplifier



Isolating Large Capacitive Loads



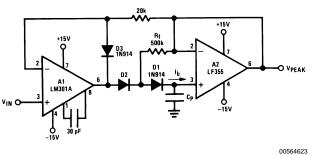
- Overshoot 6%
- t_s 10µs
- When driving large C_L , the V_{OUT} slew rate determined by C_L and $I_{OUT(MAX)}$:

$$\frac{\Delta V_{OUT}}{\Delta T} = \frac{I_{OUT}}{C_L} \simeq \frac{0.02}{0.5} \, V/\mu s = 0.04 \, V/\mu s \text{ (with } C_L \text{ shown)}$$

LF155/LF156/LF256/LF257/LF355/LF356/LF357

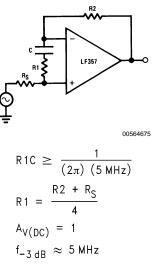
Typical Applications (Continued)

Low Drift Peak Detector

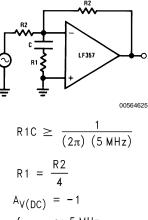


- By adding D1 and R_{f} , V_{D1} =0 during hold mode. Leakage of D2 provided by feedback path through R_{f} .
- Leakage of circuit is essentially $\rm I_b$ (LF155, LF156) plus capacitor leakage of Cp.
- Diode D3 clamps V_{OUT} (A1) to $V_{\text{IN}}-V_{\text{D3}}$ to improve speed and to limit reverse bias of D2.
- Maximum input frequency should be << $1/2\pi R_f C_{D2}$ where C_{D2} is the shunt capacitance of D2.

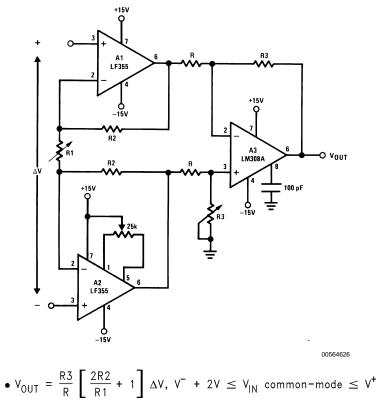




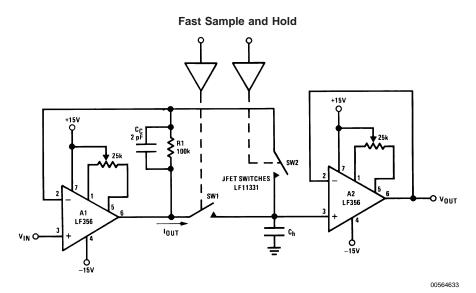
Inverting Unity Gain for LF157







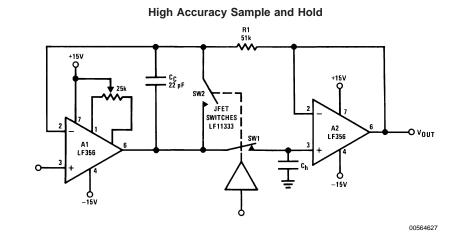
- System $V_{\rm OS}$ adjusted via A2 $V_{\rm OS}$ adjust
- Trim R3 to boost up CMRR to 120 dB. Instrumentation amplifier resistor array recommended for best accuracy and lowest drift



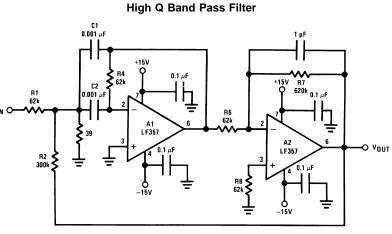
- Both amplifiers (A1, A2) have feedback loops individually closed with stable responses (overshoot negligible)
- Acquisition time T_A, estimated by:

$$\begin{split} & \mathsf{T}_{\mathsf{A}} \, \cong \left[\frac{2\mathsf{R}_{\mathsf{ON}}, \, \mathsf{V}_{\mathsf{IN}}, \, \mathsf{C}_{\mathsf{h}}}{\mathsf{S}_{\mathsf{r}}} \right] \, ^{1/2} \text{ provided that:} \\ & \mathsf{V}_{\mathsf{IN}} \, < \, 2\pi\mathsf{S}_{\mathsf{r}} \, \mathsf{R}_{\mathsf{ON}}\mathsf{C}_{\mathsf{h}} \text{ and } \mathsf{T}_{\mathsf{A}} \, > \, \frac{\mathsf{V}_{\mathsf{IN}}\mathsf{C}_{\mathsf{h}}}{\mathsf{I}_{\mathsf{OUT}(\mathsf{MAX})}}, \, \mathsf{R}_{\mathsf{ON}} \text{ is of SW1} \\ & \mathsf{If inequality not satisfied:} \, \mathsf{T}_{\mathsf{A}} \, \cong \, \frac{\mathsf{V}_{\mathsf{IN}}\mathsf{C}_{\mathsf{h}}}{20 \, \mathsf{mA}} \end{split}$$

- LF156 develops full S_r output capability for $V_{IN} \geq 1V$
- Addition of SW2 improves accuracy by putting the voltage drop across SW1 inside the feedback loop
- Overall accuracy of system determined by the accuracy of both amplifiers, A1 and A2



- By closing the loop through A2, the V_{OUT} accuracy will be determined uniquely by A1. No V_{OS} adjust required for A2.
- T_A can be estimated by same considerations as previously but, because of the added propagation delay in the feedback loop (A2) the overshoot is not negligible.
- · Overall system slower than fast sample and hold
- R1, C_C: additional compensation
- Use LF156 for
 - Fast settling time
 - Low V_{OS}

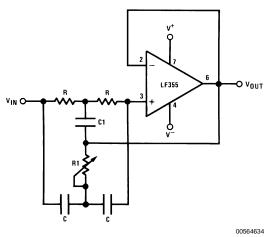


- By adding positive feedback (R2)
- Q increases to 40
- f_{BP} = 100 kHz

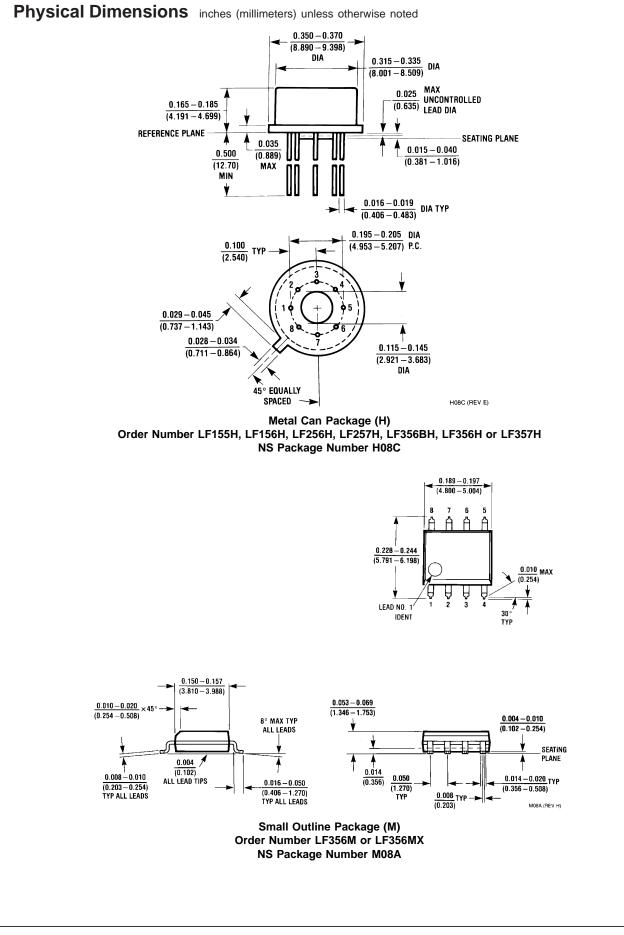
$$\frac{V_{OUT}}{V_{IN}} = 10 \sqrt{\overline{Q}}$$

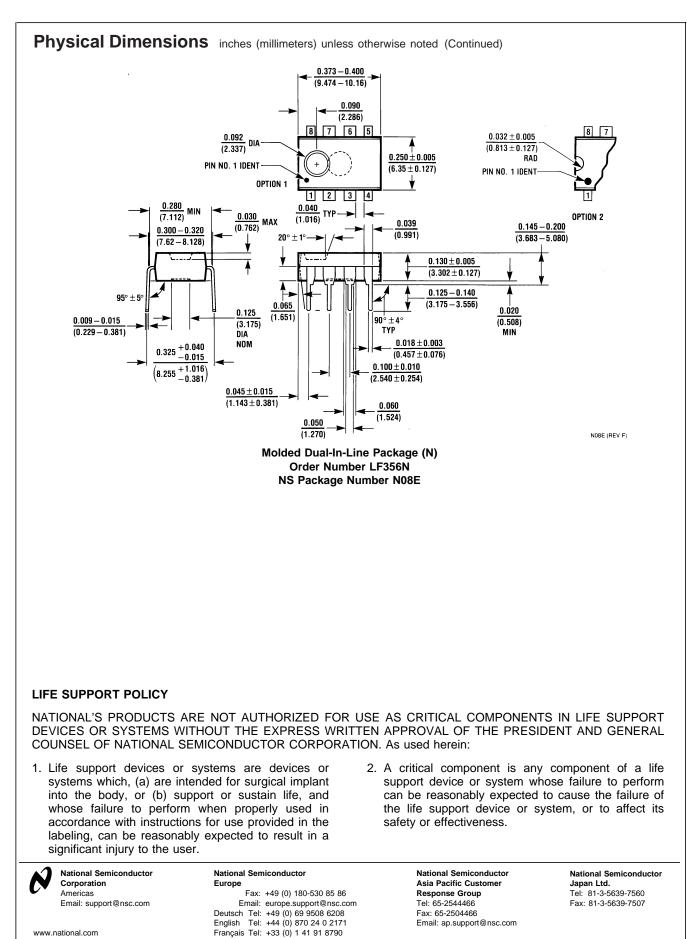
- Clean layout recommended
- Response to a 1Vp-p tone burst: 300µs

High Q Notch Filter



- 2R1 = R = 10MΩ 2C = C1 = 300pF
- Capacitors should be matched to obtain high Q
- $f_{NOTCH} = 120$ Hz, notch = -55 dB, Q > 100
- Use LF155 for
 - Low I_B
 - Low supply current





LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.

<u>Products > Analog - Amplifiers > Operational Amplifiers > General Purpose > LF356</u>

LF356 Product Folder

JFET Input Operational Amplifiers

GeneralDescription	Datasheet	<u>Package</u> <u>& Models</u>	· · ·		<u>Application</u> <u>Notes</u>				
Parametric Table		Parametric Table							
Channels (Channels)	1	Maximum	Supply Voltage	(Volt)	36, 44				
Input Output Type	Vcm to V+, Not R-I	R Offset Volt	Offset Voltage, Max (mV)						
	Out	Input Bias	Input Bias Current, Temp Max (nA)						
Bandwidth, typ (MHz)	5, 12	Output Cu	Output Current, typ (mA)						
Slew Rate, typ (Volts/usec)	12	Voltage No		12					
Supply Current per Channel, typ (mA)	5	Shut down							
Minimum Supply Voltage (Volt)	10	Special Fea	Special Features						

Datasheet

Title	Size in Kbytes	Date	View Online	Download	Receive via Email
LF155 LF156 LF256 LF257 LF355 LF356 LF357 JFET Input Operational Amplifiers	1079 Kbytes	17- Dec- 01	<u>View Online</u>	Download	<u>Receive via</u> <u>Email</u>
LF155 LF156 LF256 LF257 LF355 LF356 LF357 JFET Input Operational Amplifiers (JAPANESE)	950 Kbytes		View Online	Download	Receive via

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Package Availability, Models, Samples & Pricing

Part	Pacl	kage		Models		Samples &	Budgetary Pricing		Std Pack	Package			
Number	Туре	Pins	MSL	Status	SPICE	SPICE IBIS Orders		Qty	\$US each	Size	<u>Marking</u>		
LF356M	<u>SOIC</u>	8	MSL	Full	LF356.MOD		24 Hour	1K+	114	117	K+ \$0.2990	rail of	[logo]¢2¢T
LF350M	NARROW	0	MOL	production	<u>LI 330.MOD</u>	IN/A	Buy Now	IK+	\$0.2990	95	LF356 M		

LF356MX	SOIC NARROW	8	MSL	Full production	LF356.MOD	N/A	Buy Now	1K+	\$0.2990	reel of 2500	[logo]¢2¢T LF356 M
LF356N	MDIP	8	MSL	Full production	LF356.MOD	N/A	Buy Now	1K+	\$0.3070	rail of 40	[logo]¢U¢Z¢2¢T LF 356N
LF356BH	<u>TO-5</u>	8	MSL	Full production	LF356.MOD	N/A	Buy Now	1K+	\$1.6800	box of 500	[logo]¢Z¢2¢T LF356BH
LF356H	<u>TO-5</u>	8	MSL	Full production	LF356.MOD	N/A	Buy Now	1K+	\$1.1800	box of 500	[logo]¢Z¢2¢T LF356H
LF356 MDC	Di	<u>e</u>		Full production	LF356.MOD	N/A	Samples			tray of N/A	-
LF356 MWC	Wafer		Full production	<u>LF356.MOD</u>	N/A				wafer jar of N/A	-	

General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET[™] Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Features

Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance-very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers
- Logarithmic amplifiers
- Photocell amplifiers
- Sample and Hold circuits

Design Tools

Title	Size in Kbytes	Date	Viev	w Online	Dow	nload	Receive via Email
Amplifiers Selection Guide software for Windows	7 Kbytes	12-Jun-2002	View	<u>/</u>			

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Application Notes

Title	Size in Kbytes	Date	View Online	Download	Receive via Email
AN-447: Protection Schemes for BI-FET Amplifiers and Switches	76 Kbytes	4-Nov-95	View Online	Download	Receive via Email
AN-292: Application Note 292 Applications of the LM3524 Pulse- Width-Modulator	239 Kbytes	1-May-98	View Online	Download	Receive via Email
AN-263: Sine Wave Generation Techniques	223 Kbytes	4-Nov-95	View Online	Download	Receive via Email
AN-272: Op Amp Booster Designs	171 Kbytes	9-Apr-96	View Online	Download	Receive via Email
LB-42: Get Fast Stable Response From Improved Unity-Gain Followers	83 Kbytes	28-Jun-96	View Online	Download	Receive via Email
AN-275: CMOS D/A Converters Match Most Microprocessors	124 Kbytes	4-Nov-95	View Online	Download	Receive via Email
AN-293: Control Applications of CMOS DACs	178 Kbytes	4-Nov-95	View Online	Download	Receive via Email
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AN-258: Data Acquisition Using the ADC0816 and ADC0817 8-Bit A/D Converter with On-Chip 16 Channel Multiplexer	388 Kbytes	4-Nov-95	View Online	Download	<u>Receive via Email</u>
AN-260: A 20-Bit (1 ppm) Linear Slope-Integrating A/D Converter	148 Kbytes	4-Nov-95	View Online	Download	Receive via Email
AN-294: Special Sample and Hold Techniques	133 Kbytes	4-Nov-95	View Online	Download	Receive via Email
AN-311: Application Note 311 Theory and Applications of Logarithmic Amplifiers	206 Kbytes	24-Feb-99	View Online	Download	<u>Receive via Email</u>
AN-480: A 40 MHz Programmable Video Op Amp	181 Kbytes	4-Nov-95	View Online	Download	Receive via Email

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